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UNIVERSITY OF SASKAT MIDTERM EXAMINA

Communications Electronics

Professor:

Dr. D. M. Klymyshyn

October 23, 2001

Time:

1.5 hours

Notes:

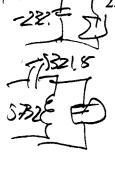
Exam is **closed book**. 1 page of formulas is allowed.

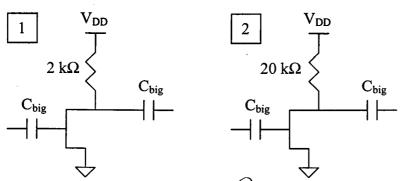
All questions are of equal value.

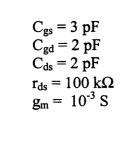
Q = 32/

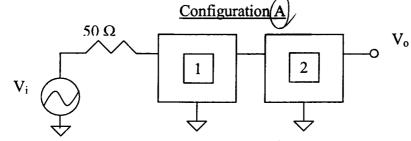
Design 2-element reactive L-type matching circuits to match a load impedance of $Z_L = 300 + j500 \Omega$ to a source impedance of $Z_S = 100 \Omega$. Estimate the **Q** of the matching circuits and choose the matching circuit with the **highest** Q.

Two small signal amplifier stages (identical FETs) are shown below (complete biasing circuitry is not shown). Estimate the 3 dB bandwidth of the cascade of the two sections, using configurations A and B as shown below. Which configuration, A or B, has higher frequency operation?

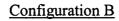


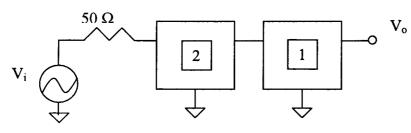






fo = 732.1kHz Config A bety



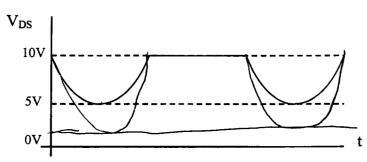


3. The waveforms at the drain of **one transistor** of a Class B **push-pull** power stage are shown below (the waveforms at the drain of the other transistor look the same but are 180 degrees out of phase).

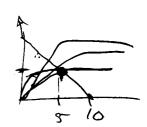
a What is the load resistance seen by the drain?

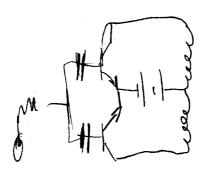
b. What is the total output power and power efficiency of the push-pull stage for the waveforms shown?
c. What is the maximum output power and efficiency assuming V_{SAT} = 2 V?

c. What is the maximum output power and efficiency assuming $V_{SAT} = 2$ V? What do you have to change to obtain this? Sketch the drain waveforms for this case. (assume that $I_{d,max} = I_{DSS} = 500$ mA, and that V_{DD} cannot be changed) V_{DS} V_{DS}



0V t





0 mA



